



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

KSB564A TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.8 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

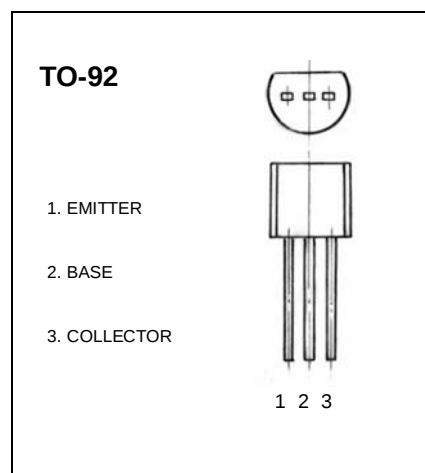
$$I_{CM}: -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -30 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 \text{ mA}, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -30\text{V}, I_E = 0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -0.1\text{A}$	70	400	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -1\text{A}, I_B = -0.1\text{A}$		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -1\text{A}, I_B = -0.1\text{A}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -10\text{mA}$	80		MHz
Output capacitance	C_{ob}	$V_{CE} = -6\text{V}, I_E = 0, f = 1 \text{ MHz}$		25	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y	G
Range	70-140	120-240	200-400